

## REMARKS

Claim 1 calls for forming a phase change memory element to be read with a voltage greater than or equal to the threshold voltage of the element.

The cited reference and the material cited in column 6 refers not to the threshold voltage, but to a threshold value. That threshold value does not correspond in any way to the claimed threshold voltage of the element.

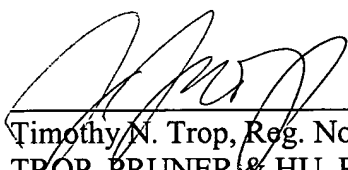
Instead, the threshold value that is referred to is the one that corresponds to the low resistance state. See column 6, lines 45 and 46 of the cited Ovshinsky patent. Thus, there is a threshold value that indicates the low resistance state. For example, referring to Figure 1, there is a range of resistance. The low resistance state would have a threshold value of resistance that would be indicative that you have programmed from the high resistance state to the low resistance state.

The way you determine whether you are in the low resistance state or not is whether or not you are below the threshold resistance value corresponding to the low resistance state. Certainly, nothing in this language has anything to do with threshold voltage. And even if it did have something to do with threshold voltage, it talks about going below the threshold value, not applying a voltage greater than the threshold voltage.

Therefore, reconsideration of the rejection of claim 1, its dependent claims, claim 6, its dependent claims, and claim 17 and its dependent claims is respectfully requested.

Respectfully submitted,

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